



Press Contact:

Eileen Elam  
KJ Communications, Inc.  
Tel: +1 408 927-7753  
[eileen@kjcompr.com](mailto:eileen@kjcompr.com)

## **Innovative Silicon's Serguei Okhonin to Speak about "Disruptive Technologies for More Moore" at ESSDERC**

*Industry visionary highlighting impending challenges for DRAM and need for replacement technology*

SANTA CLARA, Calif. — September 3, 2009 — Innovative Silicon, Inc. (ISi), developer of the Z-RAM® zero-capacitor floating body memory (FB) technology, today announced that the company's co-founder and chief scientist, Dr. Serguei Okhonin, is participating in a tutorial at the 2009 [ESSDERC](#) conference titled "Disruptive Technologies for More Moore." Dr. Okhonin is covering the memory advancements that must be adopted to enable semiconductor technologies to effectively scale to sub-45nm process geometries. The tutorial will be given on Monday, September 14, 2009 at the Divani Caravel Hotel in Athens, Greece.

### **About Dr. Okhonin's Presentation**

Dr. Okhonin has long recognized that Dynamic Random Access Memory (DRAM), which was first released by Intel in 1970, is running out of steam. The basic DRAM memory cell, consisting of a transistor and complex capacitor element, is becoming increasingly difficult to scale to smaller process geometries. While the DRAM industry has achieved miraculous results over the years by packing more and more memory bits onto ever smaller silicon die and selling it for cents, this is no longer feasible. Dr. Okhonin will cover the next frontier of memory technologies: floating body memories.

Dr. Okhonin is one of several speakers that will present on the "Disruptive Technologies for More Moore" topic. The tutorial is being led by Professor Jean-Pierre Colinge of Tyndall National Institute. Other speakers include: Professor Adrian M. Ionescu of Ecole Polytechnique Fédérale de Lausanne, Dr. Takayuki Kawahara of Hitachi, and Professor Simon Deleonibus of CEA Leti. For more information on the topic, see [http://www.essderc2009.org/files/Tutorial\\_moremoore.pdf](http://www.essderc2009.org/files/Tutorial_moremoore.pdf).

## **About ESSDERC**

The aim of the ESSDERC, which takes place in conjunction with the ESSCIRC conference, is to provide an annual European forum for the presentation and discussion of recent advances in solid-state devices and circuits.

ESSDERC and its sister conference ESSCIRC are governed by a single Steering Committee. The increasing level of integration for system-on-chip design made available by advances in silicon technology is stimulating more than ever before the need for deeper interaction among technologists, device experts, and circuit and system designers. While keeping separate Technical Program Committees, ESSDERC and ESSCIRC will share Plenary Keynote Presentations and Joint Sessions bridging both communities. For more information, see <http://www.essderc2009.org/>

## **About Innovative Silicon**

Innovative Silicon, Inc. (ISi) licenses its Z-RAM® ultra-dense memory technology to stand-alone DRAM manufacturers so they may manufacture the lowest-cost, most-advanced memory ICs. Licensees include Hynix Semiconductor for use in advanced DRAM chips. The heart of the Z-RAM technology is the “zero-capacitor,” single-transistor floating-body bit-cell that eliminates the complex capacitor found in today’s DRAM technologies – making Z-RAM the world’s lowest-cost and most-scalable memory technology. Since 2003, the company has closed \$47 million in venture capital funding, received numerous industry awards such as *IEEE Spectrum Magazine’s* “2007 Emerging Technology Most Likely to Succeed,” been granted dozens of patents, and established global R&D, engineering and support centers in Europe, Asia and North America. For more information see [www.z-ram.com](http://www.z-ram.com).

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